



BCR08AM-12

Triac

Low Power Use

REJ03G0343-0100

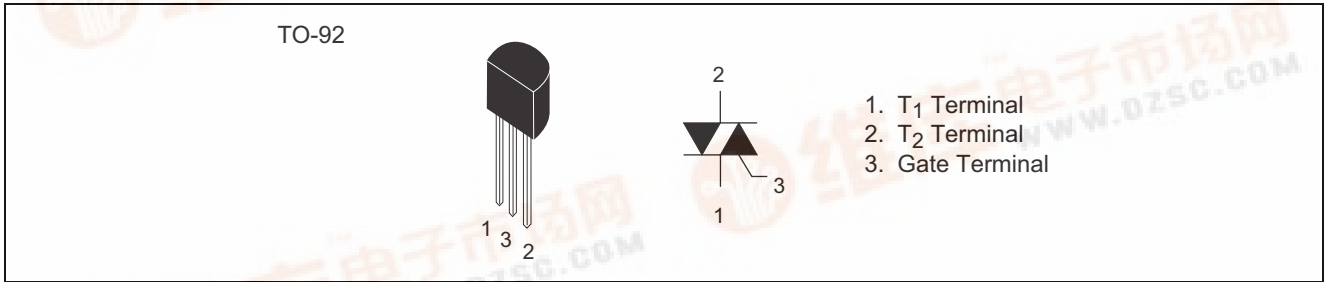
Rev.1.00

Aug.20.2004

Features

- $I_{T(RMS)}$: 0.8 A
- V_{DRM} : 600 V
- I_{RGTI} , I_{RGTIII} : 5 mA
- Planar Passivation Type

Outline



Applications

Electric fan, air cleaner, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V



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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	0.8	A	Commercial frequency, sine full wave 360° conduction, $T_c = 56^\circ\text{C}$
Surge on-state current	I_{TSM}	8	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	0.26	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	1	W	
Average gate power dissipation	$P_{G(AV)}$	0.1	W	
Peak gate voltage	V_{GM}	6	V	
Peak gate current	I_{GM}	0.5	A	
Junction temperature	T_j	- 40 to +125	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +125	$^\circ\text{C}$	
Mass	—	0.23	g	Typical value

Notes: 1. Gate open.

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Repetitive peak off-state current	I_{DRM}	—	—	1.0	mA	$T_j = 125^\circ\text{C}$, V_{DRM} applied	
On-state voltage	V_{TM}	—	—	2.0	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 1.2\text{ A}$, Instantaneous measurement	
Gate trigger voltage ^{Note2}	II	V_{RGTI}	—	—	2.0	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	III	V_{RGTIII}	—	—	2.0	V	
Gate trigger current ^{Note2}	II	I_{RGTI}	—	—	5	mA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	III	I_{RGTIII}	—	—	5	mA	
Gate non-trigger voltage	V_{GD}	0.1	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$	
Thermal resistance	$R_{th(j-c)}$	—	—	60	$^\circ\text{C/W}$	Junction to case ^{Note3}	
Critical-rate of rise of off-state commutating voltage ^{Note4}	$(dv/dt)_c$	0.5	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$	

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

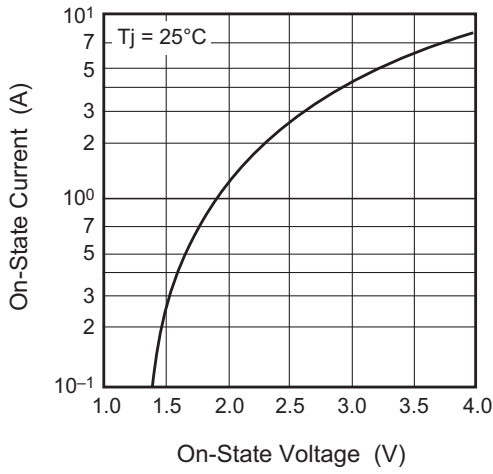
3. Case temperature is measured at the T_2 terminal 1.5 mm away from the molded case.

4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

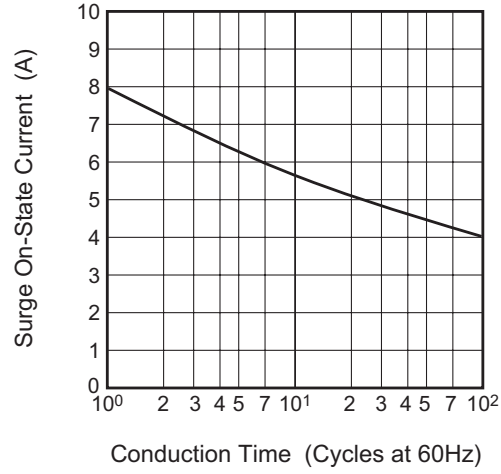
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -0.4\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

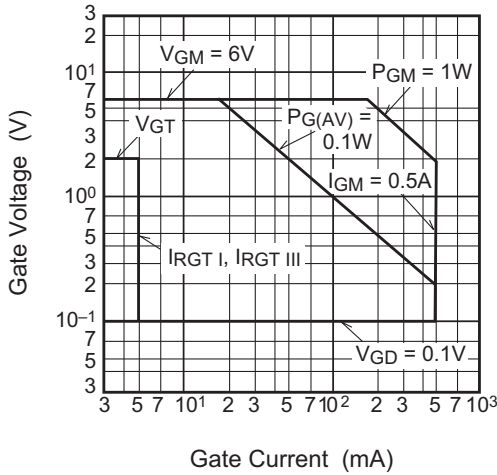
Maximum On-State Characteristics



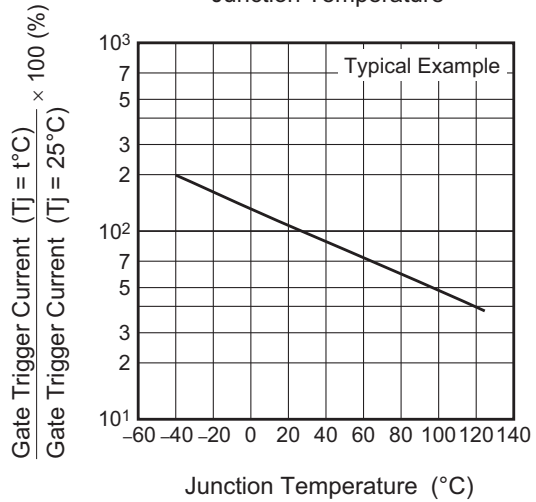
Rated Surge On-State Current



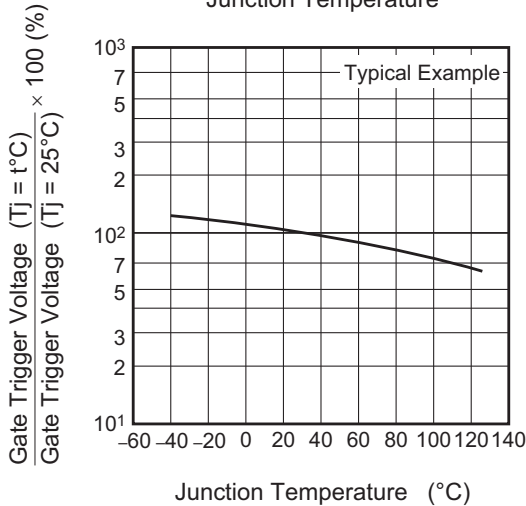
Gate Characteristics (II and III)



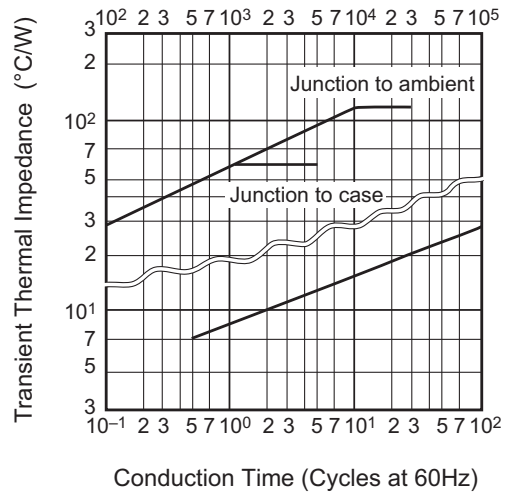
Gate Trigger Current vs. Junction Temperature

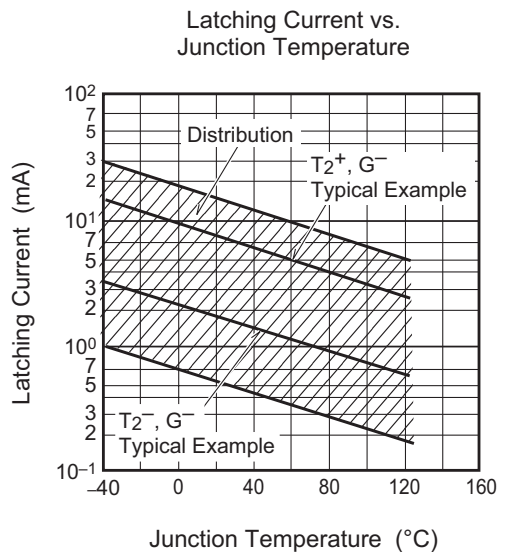
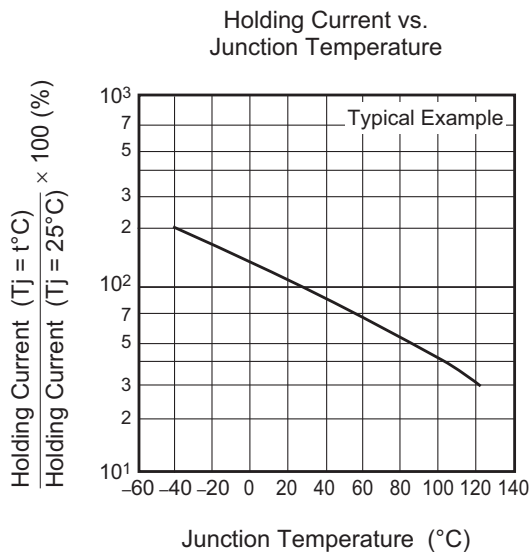
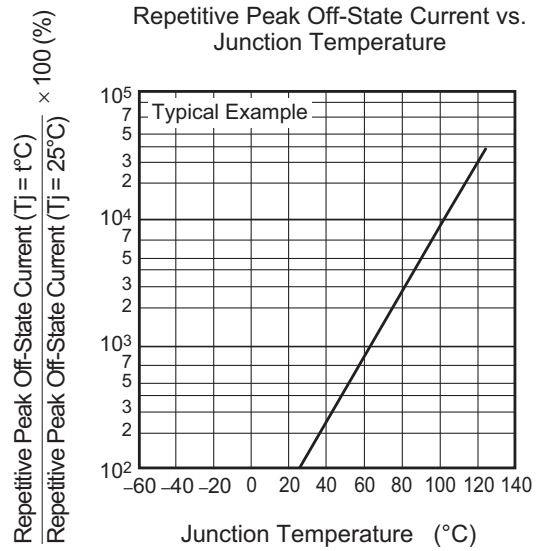
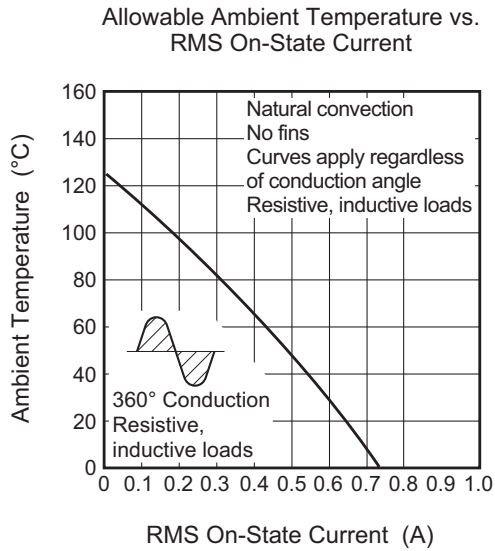
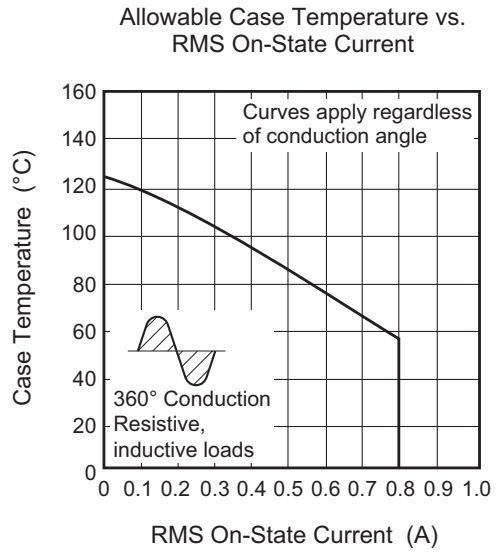
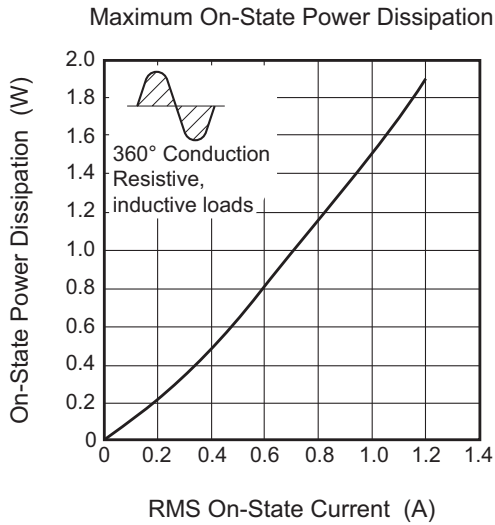


Gate Trigger Voltage vs. Junction Temperature

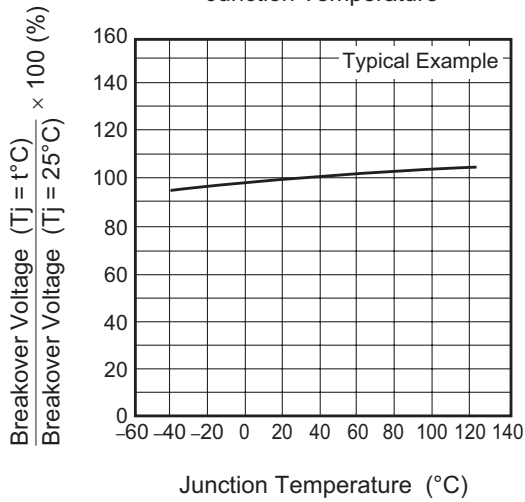


Maximum Transient Thermal Impedance Characteristics (Junction to case, Junction to ambient)

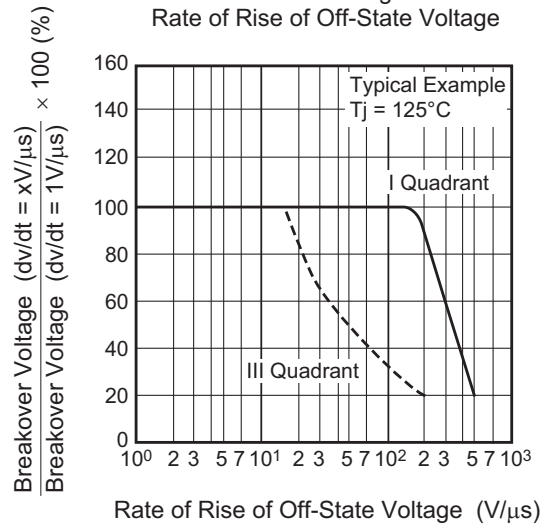




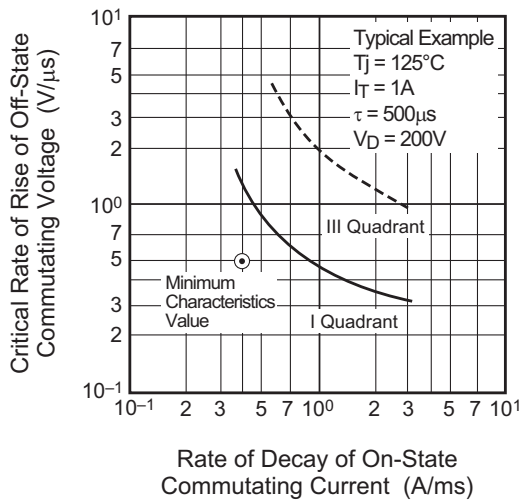
Breakover Voltage vs. Junction Temperature



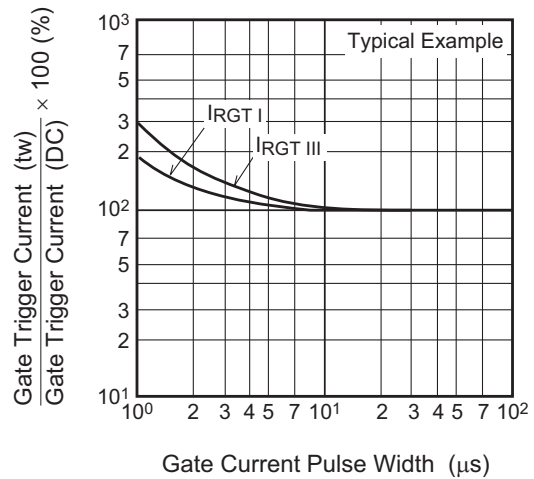
Breakover Voltage vs. Rate of Rise of Off-State Voltage



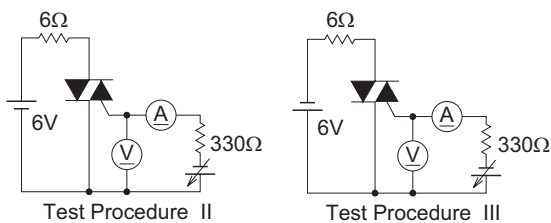
Commutation Characteristics



Gate Trigger Current vs. Gate Current Pulse Width



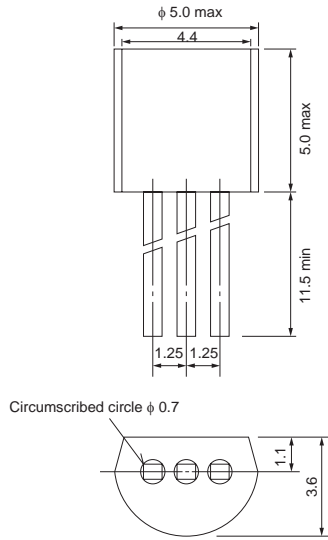
Gate Trigger Characteristics Test Circuits



Package Dimensions

TO-92

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	Conforms	0.23	Cu alloy



Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	500	Type name +A	BCR08AM-12A
Lead form	Vinyl sack	500	Type name +A – Lead forming code	BCR08AM-12A-A6
Form A8	Taping	2000	Type name +A – TB	BCR08AM-12A-TB

Note : Please confirm the specification about the shipping in detail.

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